	7 BRS	6 BRS		5 BRS				
	۲7	Г6	•••••	5	L4 L5	L3 L4		
	162096	152617		121646		<u> </u>	85 85	20067 14515 349 307085
	(degree or deg?) near2 ("100" or "150" or "200" or "250")	(nitrog\$4 near2 (oxygen or oxide)) or (no near2 gas\$4)	(nitrog\$4 near2 (oxygen or oxide))		nitrogen or "n.sub.2"	·	or grow\$4 or	
IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT;	USPAT; r US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	JPO; DERWENT; IBM_TDB	USPAT;	USPAT; JPO; DERWENT; IBM_TDB USPAT; USPAT;	USPAT; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; JPO; DERWENT; JPO; DERWENT; JPO; DERWENT; JROPAT;		USPAT; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

		hanna ann an ann an ann an ann an ann an	***************************************		
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	13 and (@ay < "2000")	18	L14	BRS	14
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	12 not 10	20	L13	BRS	13
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11 same 6 same 7	30	L12	BRS	12
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	plasma or pecvd or pcvd	311126	L11	BRS	1 1
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	9 same 2 same 6 same 7	10	L10	BRS	10
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	plasma	310108	L9	BRS	9
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	3 same 2 same 6 same 7	0	L8	BRS	œ
DBs	Search Text	Hits	F	Туре	

	20	19	18	17	16	15	
BRS	BRS	BRS	BRS	BRS	BRS	BRS	Туре
L21	L20	L19	L18	L17	L16	L15	"
336	421	œ	86095	4799	11111	252	Hits
20 and (@ay < "2000")	18 and 17 and 16	18 same 17 same 16	(complementary adj (metal adj (insulator or oxide) adj semiconducor JF adj (fet or field)) or cmos or cmis)	USPAT; 11 same gate near3 (insulator or 1 or US-PGPUB; EPO; JPO; DERWENT; dielectric) IBM_TDB	(inplant or implant or inplanting or implanting) same (resist or photoresist or pr)	(complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis) and (thicken\$4 near8 (oxide or gate near2 (insulat\$4 or dielectric)))	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; 「JPO; DERWENT; IBM_TDB	USPAT; rUS-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		DBs

	Туре	#	Hits	Search Text	DBs
22	BRS	L22	982	11 near6 gate near3 (insulator or 1 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	L23	62	18 and 22 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	L24	49	23 and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	L25	15577	plasma adj enhanc\$4 or pecvd or pcvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	L26	138	25 near6 gate near3 (insulator or 1 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	L27	4	18 and 26 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	IS&R	L28	834	((438/154) or (438/788) or (438/791)).CCLS.	USPAT; US-PGPUB